

27-34GHz Power Amplifier

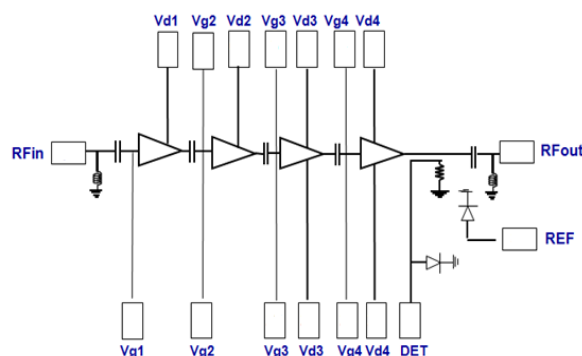
GaAs Monolithic Microwave IC

Description

The CHA6653-98F is a four stages monolithic GaAs High Power Amplifier producing 1.8 Watt output power. It is highly linear, with gain control capability and integrates a power detector. ESD protections are included.

It is designed for Telecommunication application.

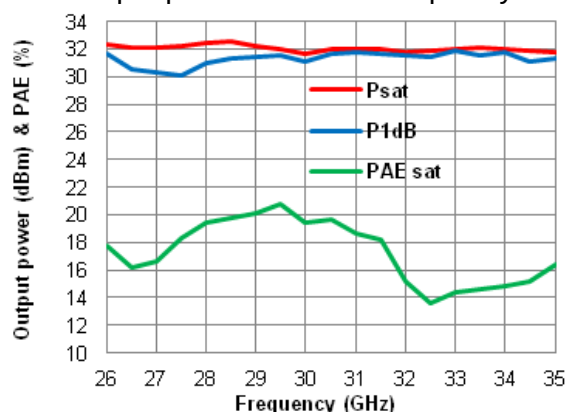
The circuit is manufactured with a pHEMT process, 0.15µm gate length.



Main Features

- Broadband performances: 27-34GHz
- 32dBm saturated power
- 38dBm OIP3
- 23dB gain
- DC bias: Vd = 6.0Volt @ Idq = 0.9A
- Chip size 3.61x3.46x0.07mm

Output power & PAE vs frequency



Main Electrical Characteristics

Tamb.= +25°C

Symbol	Parameter	Min	Typ	Max	Unit
Freq	Frequency range	27		34	GHz
Gain	Linear Gain		23		dB
Psat	Saturated output power		32		dBm
OIP3	Output IP3		38		dBm

Specifications

Tamb.= +25°C, Vd = +6.0V

Symbol	Parameter	Min	Typ	Max	Unit
Fop	Operating frequency range	27		34	GHz
Gain	Small Signal Gain		23		dB
ΔG	Gain variation in temperature		± 0.04		dB/°C
Psat	Saturated Output Power		32		dBm
OIP3	Output IP3		38		dBm
P1dB	Pout at 1dB of compression		31		dBm
PAE	PAE at saturation		17		%
CG	Gain control range		15		dB
Rlin	Input Return Loss		8		dB
Rlout	Output Return Loss		10		dB
Dr	Detection dynamic range(for output power detection up to Psat)		30		dB
Vdetect	Voltage detection V_{REF} - V_{DET} up to Psat		20 to 2000		mV
Vg	DC gate Voltage		-0.65		V
Idq	Total drain current		0.9		A

These values are representative of on-board measurements.

Electrostatic discharge sensitive device observe handling precautions!

Absolute Maximum Ratings ^{1, 2}T_{amb}. = +25°C

Symbol	Parameter	Values	Unit
V _d	Drain bias voltage	8	V
I _d	Drain bias current	2050	mA
V _g	Gate bias voltage	-2 to 0	V
V _{dg}	External drain-gate excursion	10	V
P _{in}	Maximum Input Power	+15	dBm
T _j	Maximum Junction temperature	175	°C

¹ Operation of this device above anyone of these parameters may cause permanent damage.

² These are stress rating only, and functional operation of the devices at these conditions is not implies.

Recommended Operating Range ^{3, 4}

Symbol	Parameter	Values	Unit
V _d	Drain bias voltage	5 to 6	V
I _d	Drain bias current	730 to 900	mA
V _g	Gate bias voltage	-2 to 0	V
P _{in}	Maximum peak input power overdrive	15	dBm
T _a	Operating temperature range	-40 to 95	°C

³ Electrical performances are defined for specified test conditions

⁴ Electrical performances are not guaranteed over all recommended operating conditions

Temperature Range

T _a	Operating temperature range	-40 to +95	°C
T _{stg}	Storage temperature range	-55 to +150	°C

Typical Bias ConditionsT_{amb} = +25°C

Symbol	Parameter	Values	Unit
V _{d1}	DC Drain voltage 1 st stage	6V	V
V _{d2}	DC Drain voltage 2 nd stage	6V	V
V _{d3}	DC Drain voltage 3 rd stage	6V	V
V _{d4}	DC Drain voltage 4 th stage	6V	V
V _{g1}	DC Gate voltage 1 st stage	-0.65	V
V _{g2}	DC Gate voltage 2 nd stage	-0.65	V
V _{g3}	DC Gate voltage 3 rd stage	-0.65	V
V _{g4}	DC Gate voltage 4 th stage	-0.65	V

Device thermal performances

The device thermal performances below are based on UMS rules to evaluate the junction temperature.

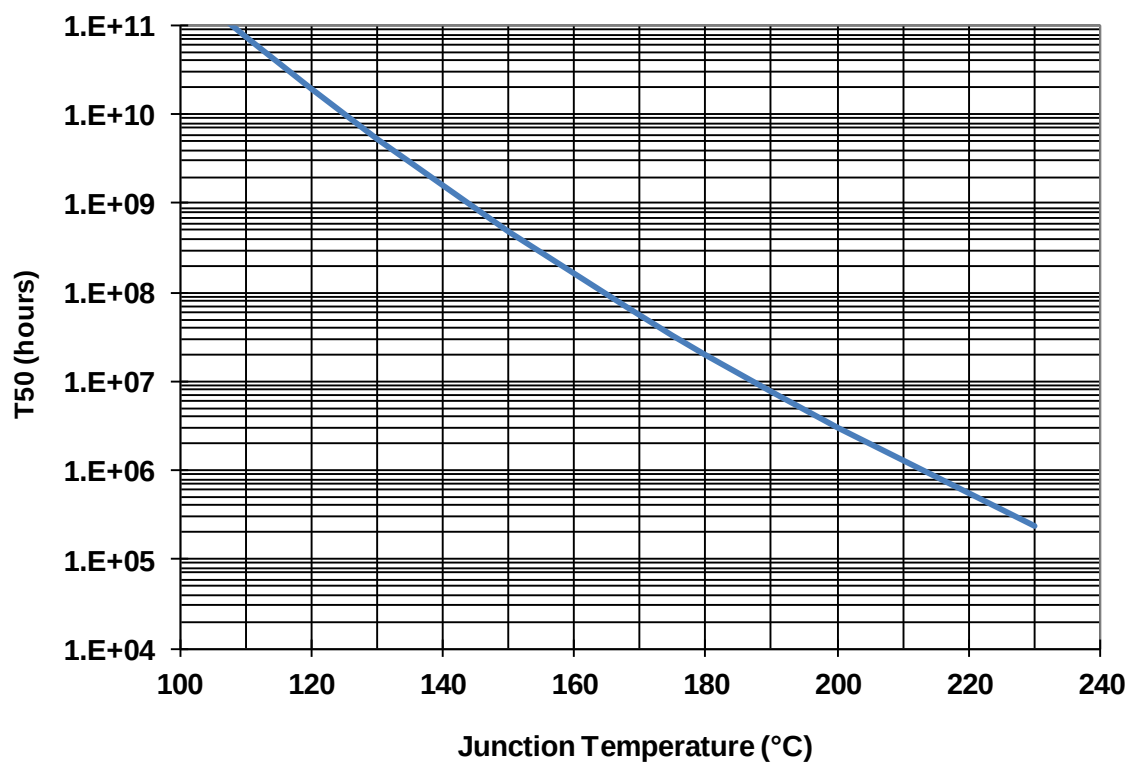
The temperature $T_{b\text{ chip}}$ is defined as the chip back side temperature.

The system maximum temperature must be adjusted in order to guarantee that T_{junction} remains below the maximum value specified in the Absolute Maximum Ratings table.

So, the PCB system must be designed to comply with this requirement.

Parameter	Biasing conditions	T_{junction} (°C)	R_{TH} (°C/W)	T50 (hours)
$R_{\text{TH}}^{(1)}$ Thermal Resistance (Back of the chip)	Vd= 6V Idq = 900mA Pdiss= 5.4W	165	14.9	9.E+07

⁽¹⁾ Assuming 85°C $T_{b\text{ chip}}$



Typical on-wafer Sij parameters (Pulsed mode)

Tamb.= +25°C, Vd = +6.0V, Id = 900mA, Pulse width = 25µs, Duty cycle = 10%

Freq (GHz)	S11 (dB)	PhS11 (°)	S12 (dB)	PhS12 (°)	S21 (dB)	PhS21 (°)	S22 (dB)	PhS22 (°)
1	-0,1	177,3	-75,4	77,7	-76,4	-64,2	-0,1	176,9
3	0,0	171,4	-83,2	-48,5	-62,7	-1,6	-0,2	172,2
4	-0,1	169,0	-84,8	-37,6	-66,6	-112,6	-0,2	169,5
5	-0,1	166,0	-86,3	60,3	-65,2	-166,2	-0,2	166,8
6	-0,1	162,9	-84,2	40,8	-70,6	-13,8	-0,2	164,0
7	-0,1	159,9	-76,0	159,5	-66,1	45,1	-0,2	160,8
8	-0,1	156,7	-70,3	-125,3	-64,9	-86,4	-0,2	157,8
9	-0,1	153,1	-80,8	-103,3	-59,1	-34,7	-0,2	154,3
10	-0,1	149,3	-73,6	-134,5	-56,7	38,0	-0,2	150,3
11	-0,1	145,5	-71,7	-127,0	-65,1	-149,1	-0,2	146,4
12	-0,1	141,3	-71,7	-168,2	-64,7	-165,9	-0,3	141,6
13	-0,1	136,5	-67,4	174,7	-63,9	126,7	-0,3	135,3
14	-0,1	131,2	-62,7	102,9	-68,6	-115,4	-0,7	125,5
15	-0,1	125,0	-73,4	119,3	-57,5	163,0	-4,9	112,5
16	-0,1	117,9	-60,2	105,5	-52,9	80,9	-2,6	144,2
17	-0,1	109,2	-59,7	22,4	-50,5	7,4	-1,2	133,5
18	-0,2	98,6	-65,3	18,2	-49,9	-23,8	-0,9	124,4
19	-0,3	84,6	-76,8	-135,5	-51,7	-47,0	-0,7	114,5
20	-0,5	65,3	-75,0	3,2	-46,2	5,2	-0,7	102,9
21	-1,1	42,7	-74,7	-114,4	-26,8	15,1	-0,9	89,3
22	-2,5	4,0	-77,9	-169,2	-9,8	-52,5	-1,5	71,2
23	-5,3	-52,7	-73,4	-3,0	3,3	-146,8	-2,9	48,5
24	-8,6	-137,5	-69,2	-151,3	12,7	110,7	-5,7	22,3
25	-10,2	140,5	-54,6	-153,1	19,3	5,0	-11,2	-4,6
26	-13,2	78,8	-57,6	161,4	24,1	-101,8	-21,8	17,2
27	-15,6	35,7	-52,0	115,5	26,0	145,9	-14,4	31,6
28	-15,0	-25,8	-53,1	83,3	25,3	50,7	-15,3	-24,1
29	-14,1	-76,5	-55,8	42,8	25,1	-34,8	-18,8	-69,8
30	-14,1	-90,9	-49,9	-1,5	24,4	-119,2	-18,9	-47,3
31	-11,8	-104,7	-49,7	-28,6	24,0	162,8	-12,8	-75,1
32	-10,8	-129,4	-48,2	-28,9	24,4	82,4	-11,2	-104,5
33	-13,9	-142,8	-47,9	-74,4	24,5	-2,5	-11,8	-121,6
34	-18,2	-105,3	-52,8	-95,6	25,0	-94,5	-14,4	-130,5
35	-11,2	-86,9	-53,0	-159,9	25,2	158,1	-22,5	-87,0
36	-6,9	-90,5	-54,2	-178,0	21,9	31,1	-8,0	-67,7
37	-3,6	-108,7	-65,5	26,1	13,3	-97,6	-4,1	-96,2
38	-2,7	-126,8	-56,5	-99,6	0,1	163,7	-3,1	-113,7
39	-2,3	-136,9	-49,1	-173,1	-12,5	93,5	-2,3	-129,1
40	-2,0	-143,8	-53,4	92,0	-24,1	27,6	-2,0	-140,5

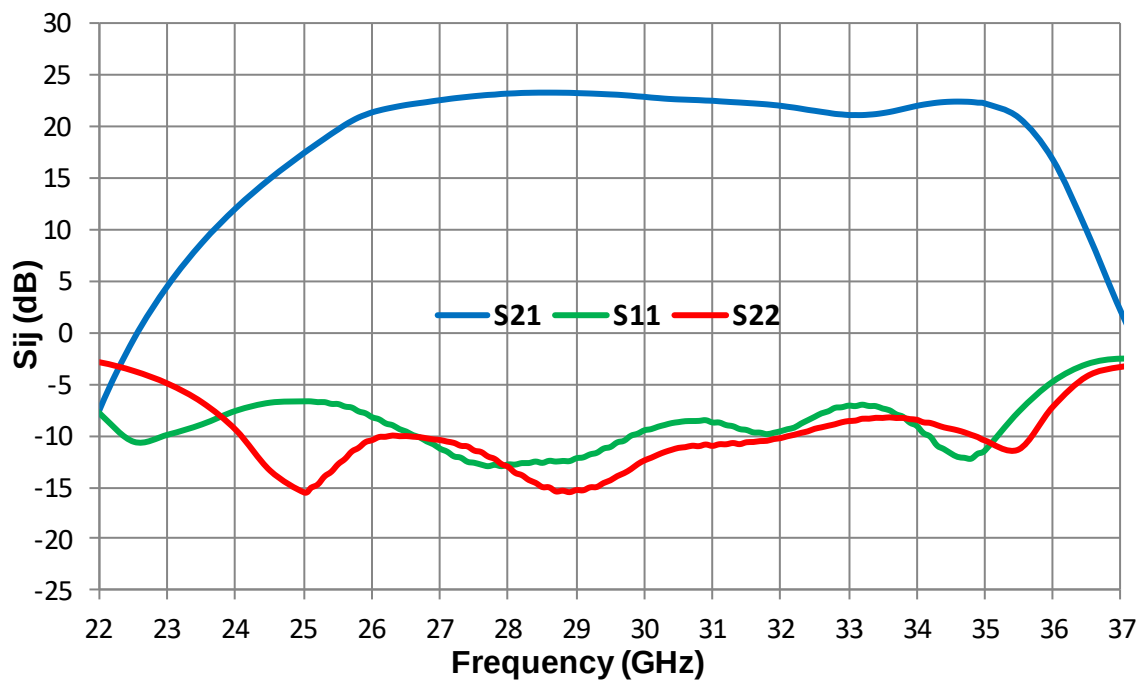
Typical Board Measurements (CW)

Tamb. = +25°C, Vd = +6V, Idq = 900mA & Vd = +5V, Idq = 730mA

Measurement performed in the access plans of the die.

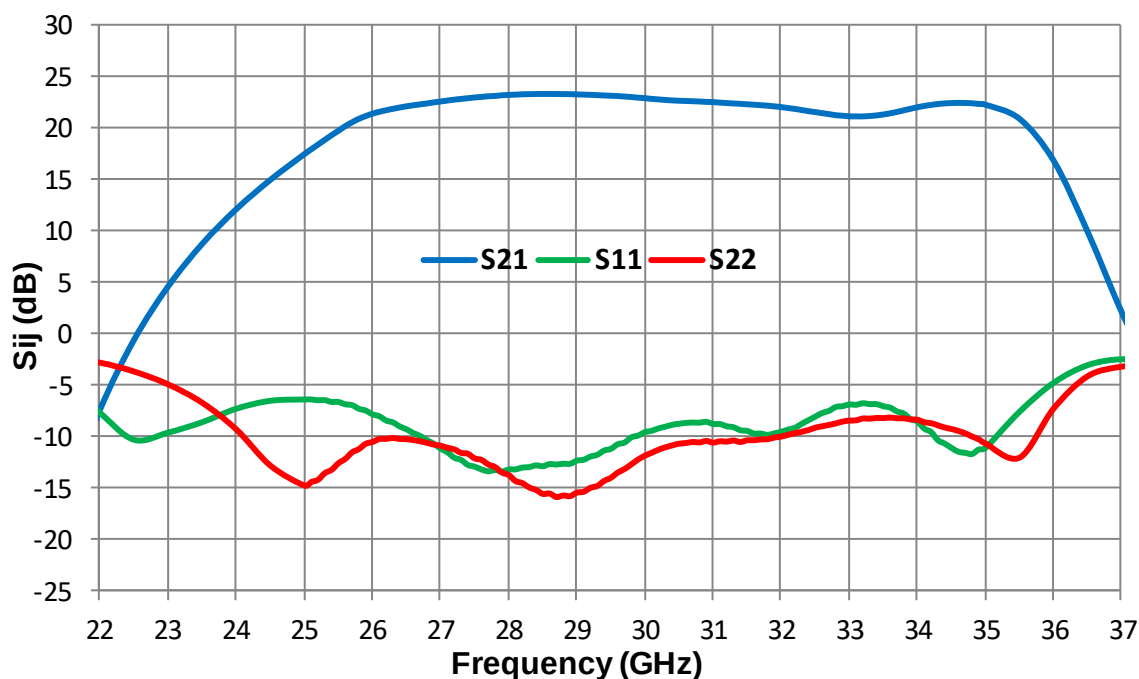
Gain & Return Losses versus Frequency

Vd = +6V, Idq = 900mA



Gain & Return Losses versus Frequency

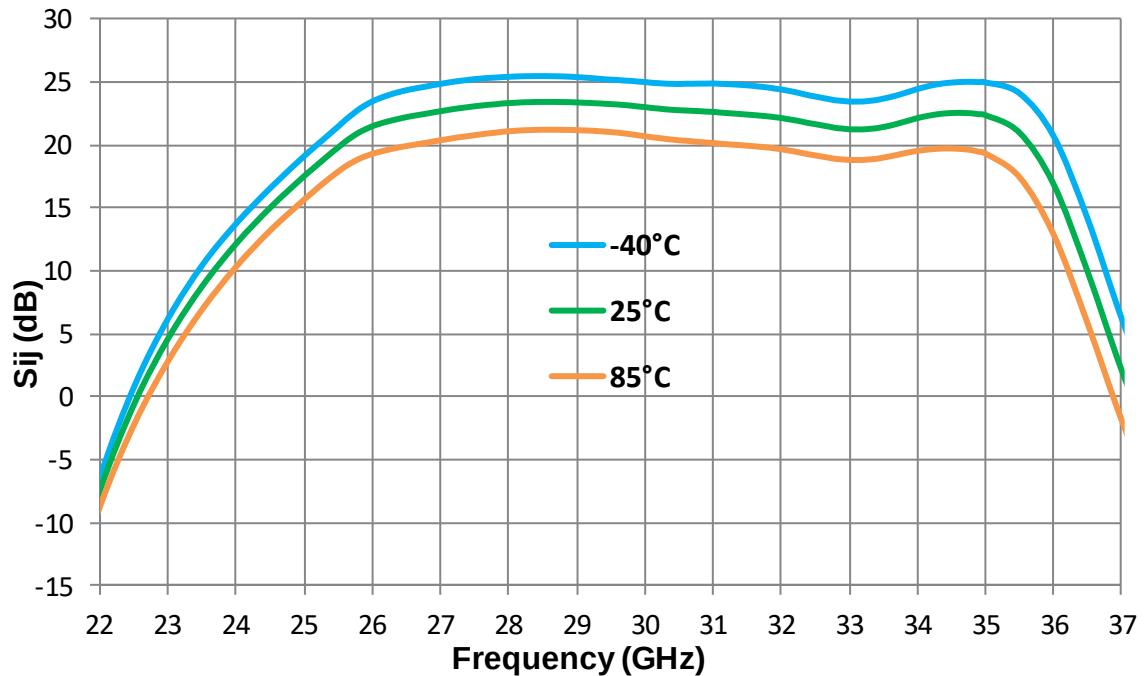
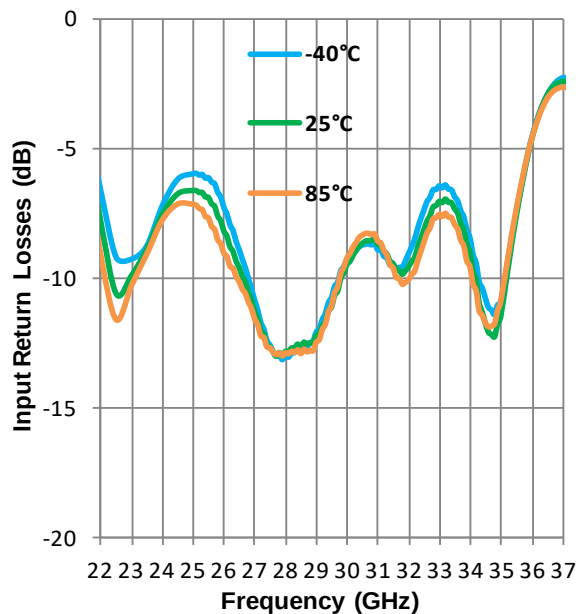
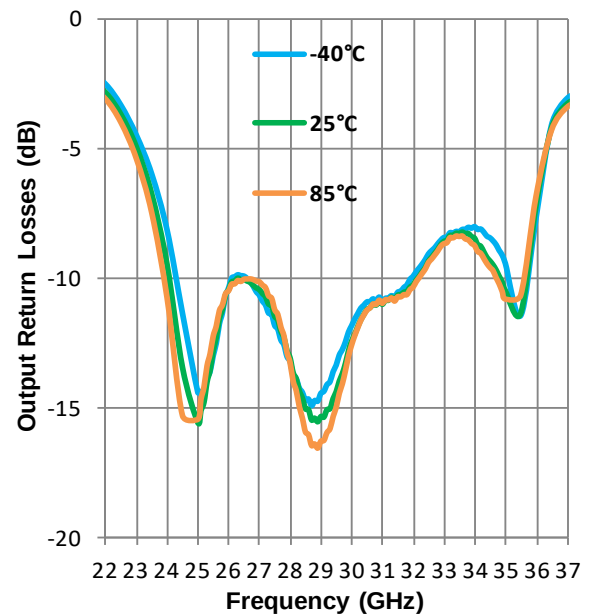
Vd = +5V, Idq = 730mA



Typical Measurements on a probe compatible Board (CW)

Tamb.= +25°C, Vd = +6.0V, Idq = 900mA

Measurement performed in the access plans of the die.

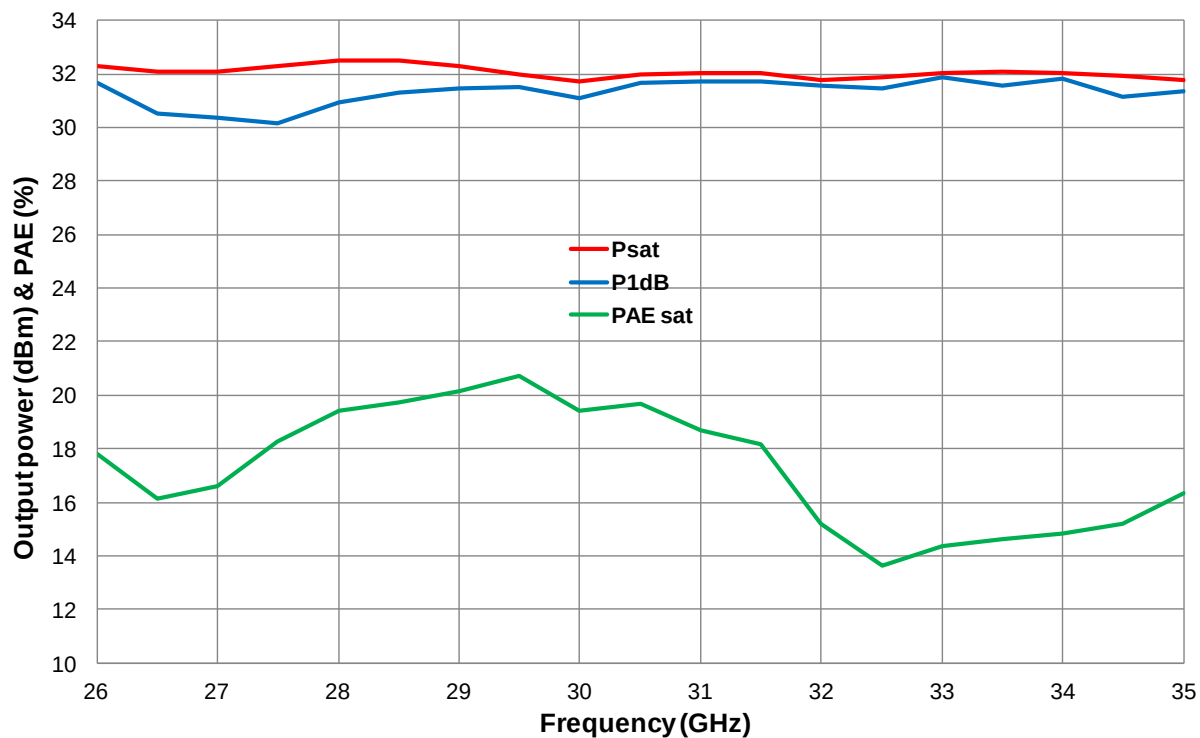
Gain versus Frequency in Temperature**Input Return Losses versus Frequency in Temperature****Output Return Losses versus Frequency in Temperature**

Typical Board Measurements (CW)

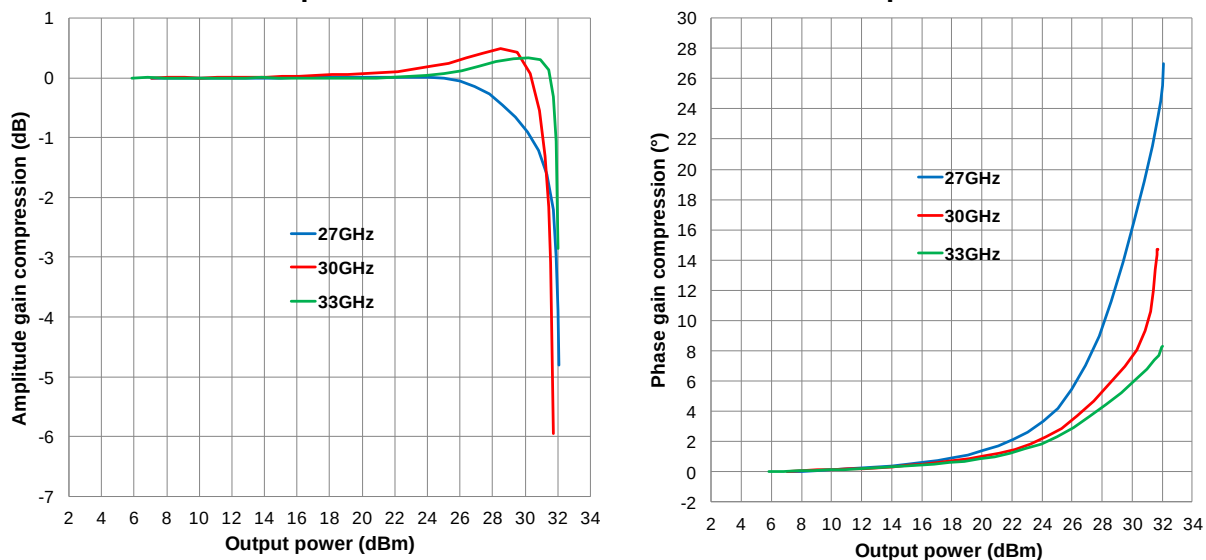
Tamb.= +25°C, Vd = +6.0V, Idq = 900mA

Measurement performed in the access plans of the die.

Output Power & PAE versus Frequency



Gain Amplitude & Gain Phase variation versus Output Power

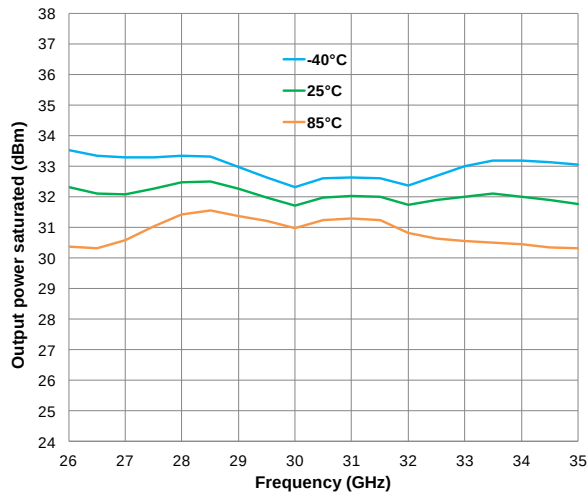


Typical Board Measurements (CW)

Tamb.= +25°C, Vd = +6.0V, Idq = 900mA & Vd = +5V, Idq = 730mA

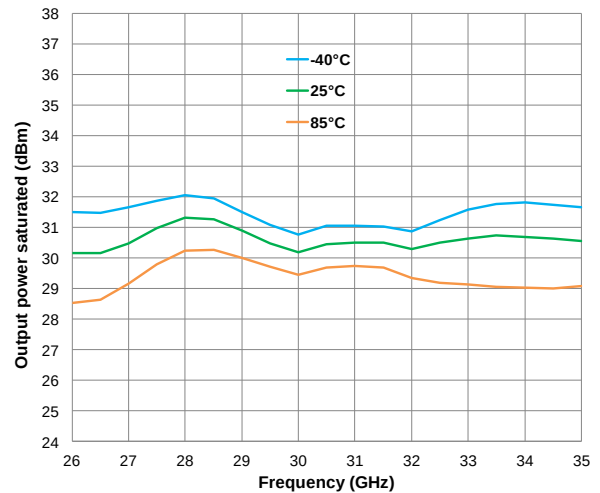
Saturated Power versus Frequency in Temperature

Vd = +6V, Idq = 900mA



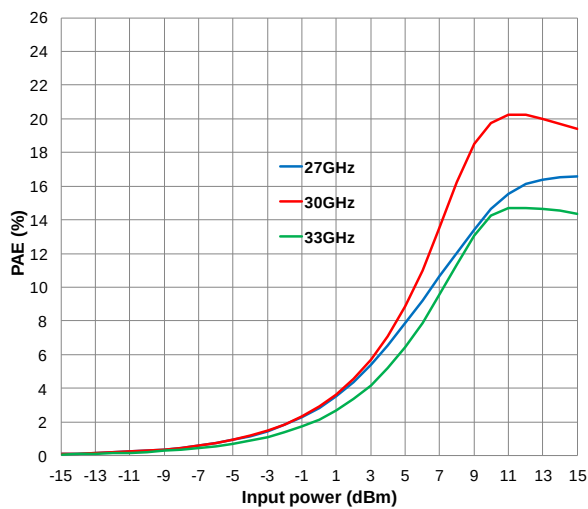
Saturated Power versus Frequency in Temperature

Vd = +5V, Idq = 730mA



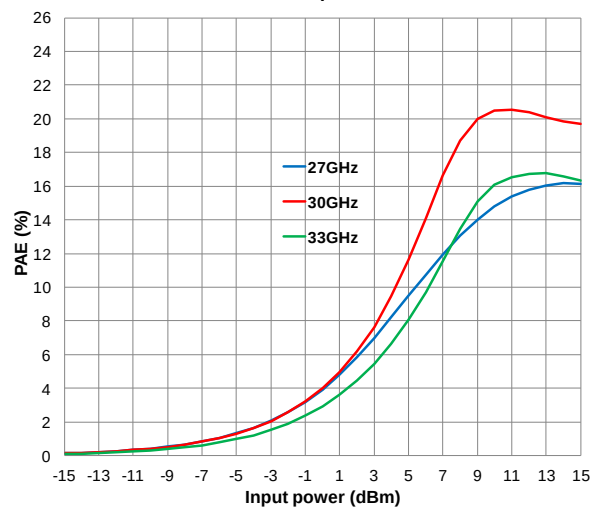
PAE versus Input Power

Vd = +6V, Idq = 900mA



PAE versus Input Power

Vd = +5V, Idq = 730mA



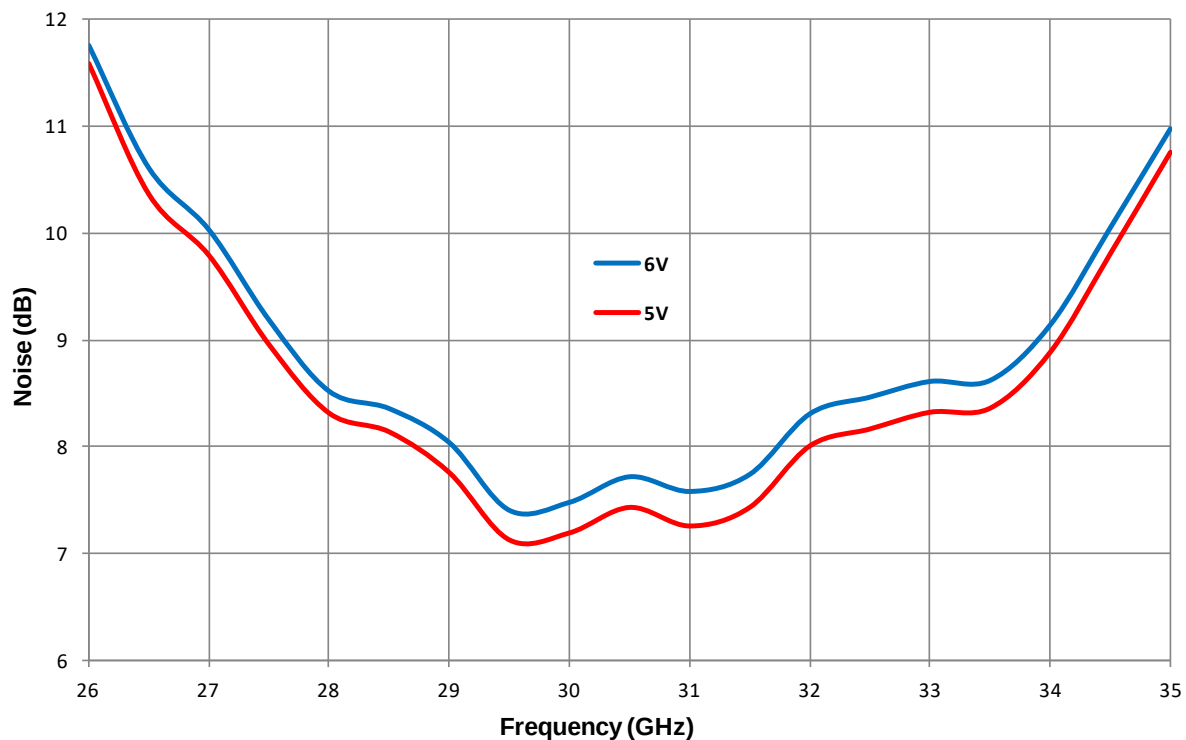
Typical Board Measurements (CW)

Tamb.= +25°C, Vd = +6.0V, Idq = 900mA & Vd = +5V, Idq = 730mA

Noise Figure versus Frequency

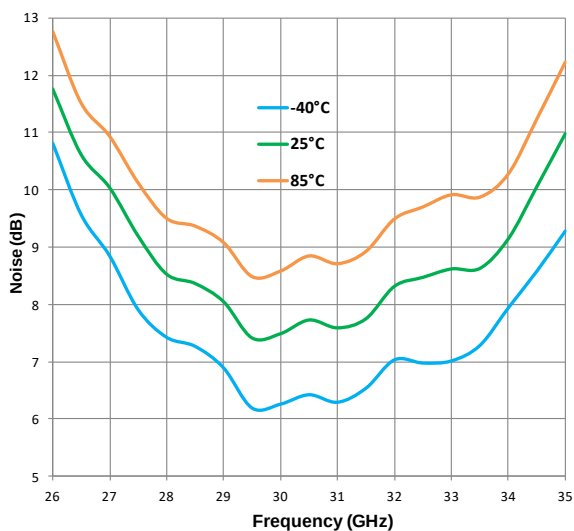
Vd = +6V, Idq = 900mA

Vd = +5V, Idq = 730mA



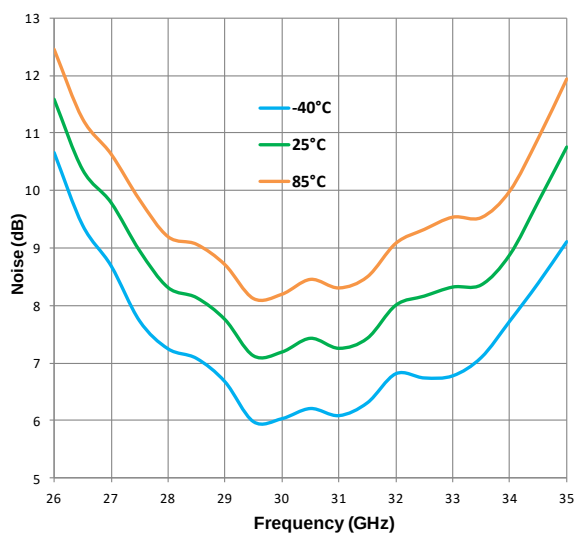
Noise Figure versus Frequency in Temperature

Vd = +6V, Idq = 900mA



Noise Figure versus Frequency in Temperature

Vd = +5V, Idq = 730mA

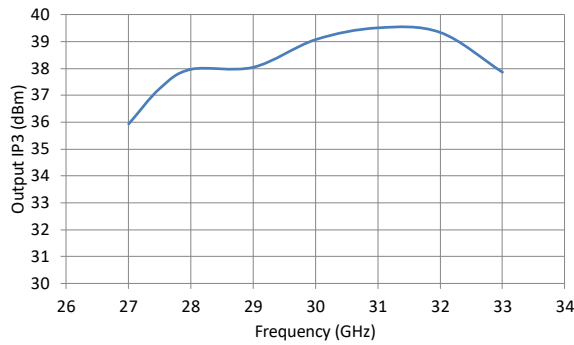


Typical Board Measurements (CW)

Tamb.= +25°C, Vd = +6.0V, Idq = 900mA & Vd = +5V, Idq = 730mA

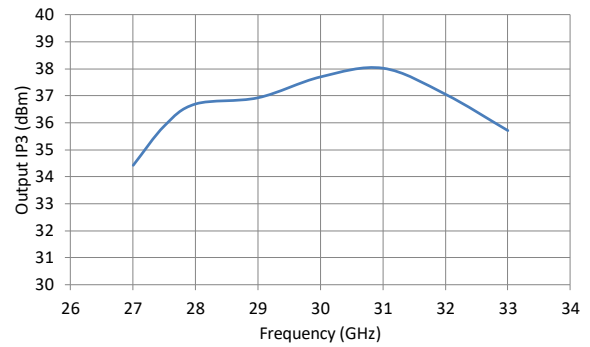
Output IP3 versus Frequency

Vd = +6V, Idq = 900mA



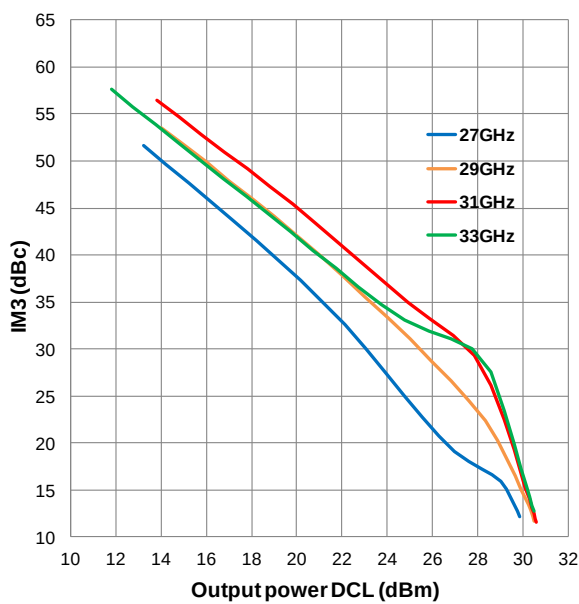
Output IP3 versus Output Power

Vd = +5V, Idq = 730mA



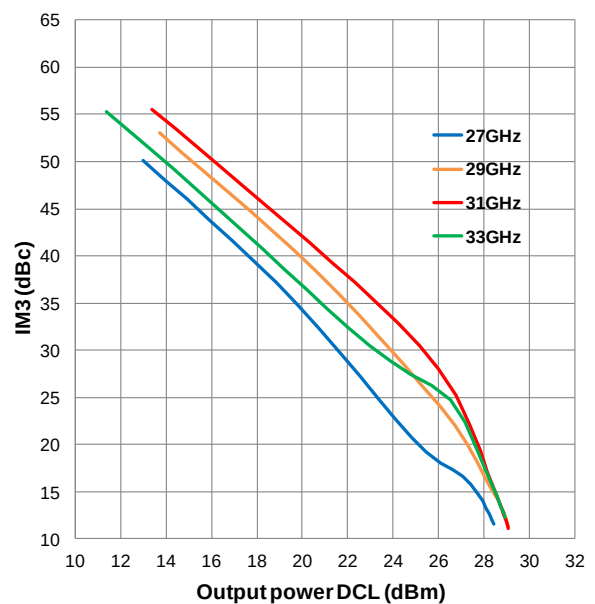
Output IM3 versus Output Power

Vd = +6V, Idq = 900mA



Output IM3 versus Output Power

Vd = +5V, Idq = 730mA

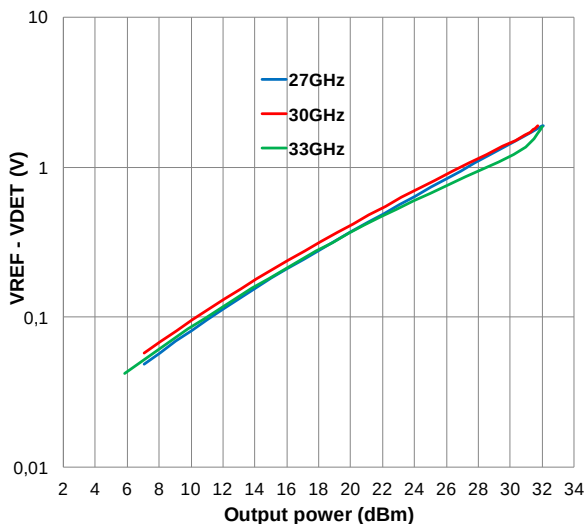


Typical Board Measurements (CW)

Tamb.= +25°C, Vd = +6.0V, Idq = 900mA & Vd = +5V, Idq = 730mA

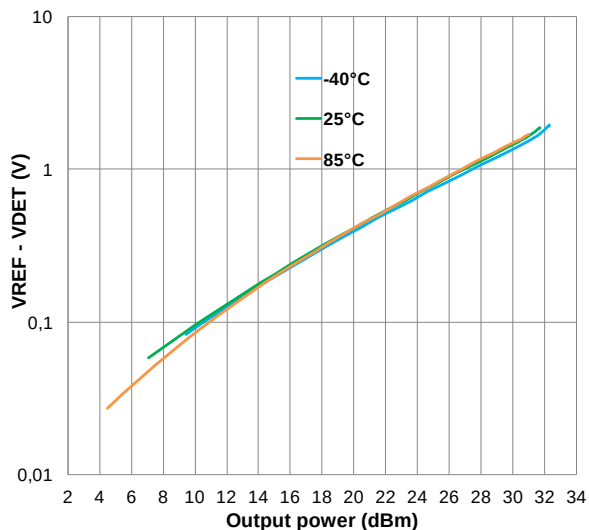
Power Detector versus Output Power

Vd = +6V, Idq = 900mA



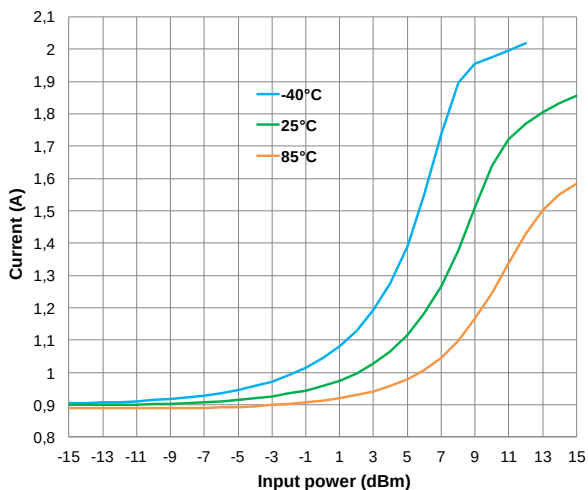
Power Detector versus Output Power & Temperature at 30GHz

Vd = +6V, Idq = 900mA



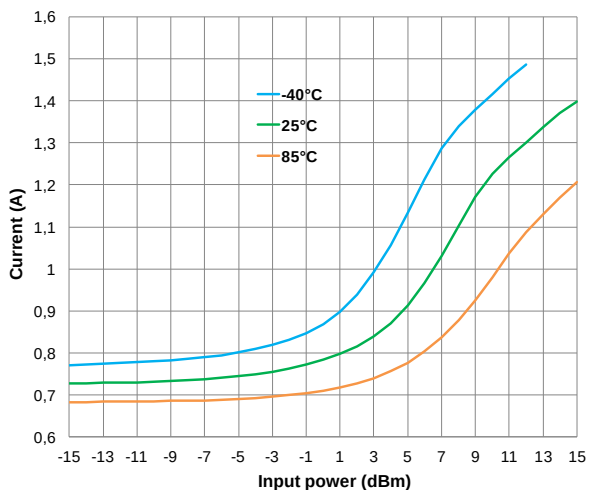
Total Drain Current versus Output Power at 32.5GHz

Vd = +6V, Idq = 900mA

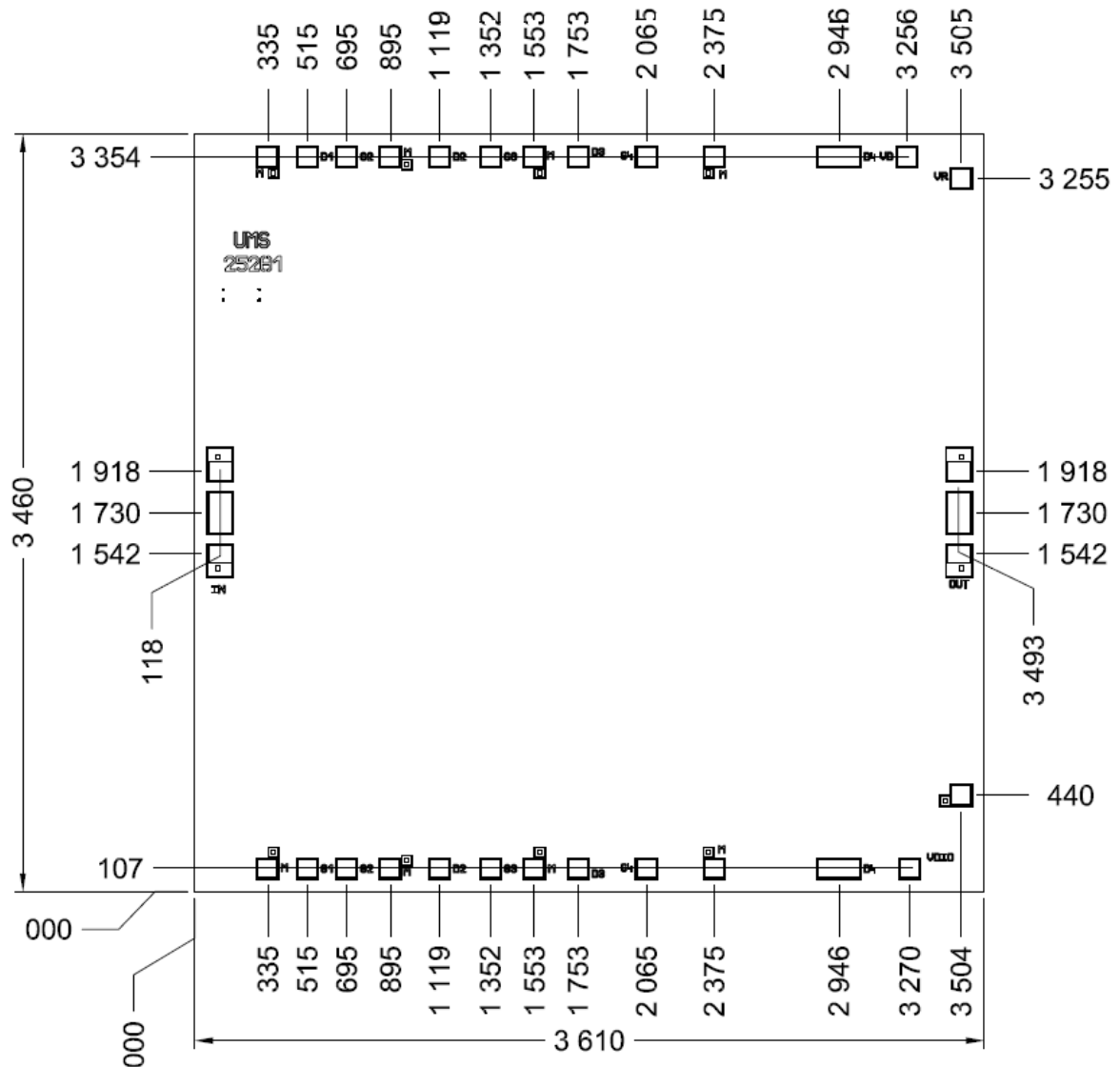


Total Drain Current versus Output Power at 32.5GHz

Vd = +5V, Idq = 730mA



Mechanical data



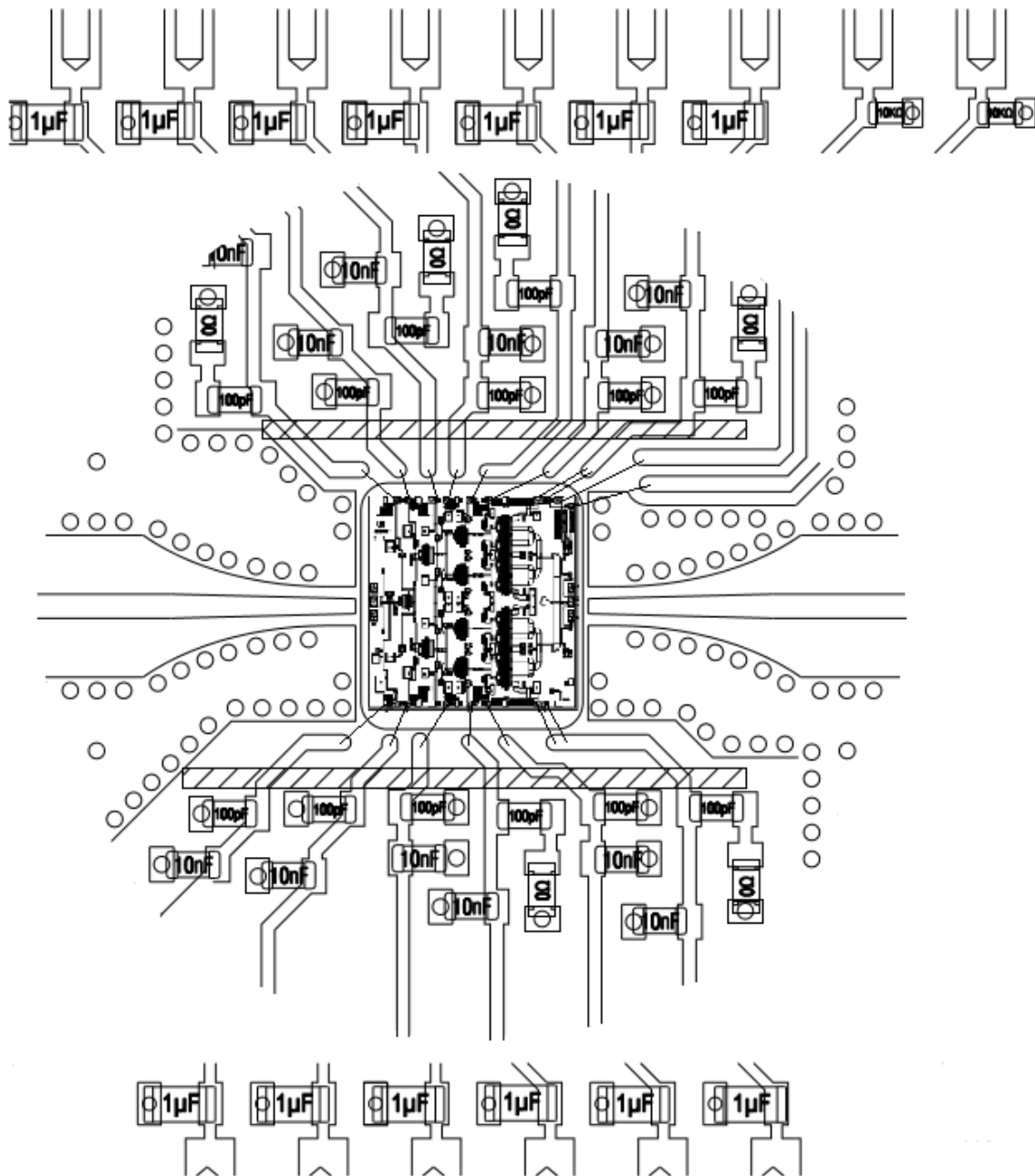
Chip thickness: 70μm.

All dimensions are in micrometers

DC pad size: 83μm x 83 μm (BCB opening)

RF pad size: 105μm x 186 μm (BCB opening)

Recommended assembly plan

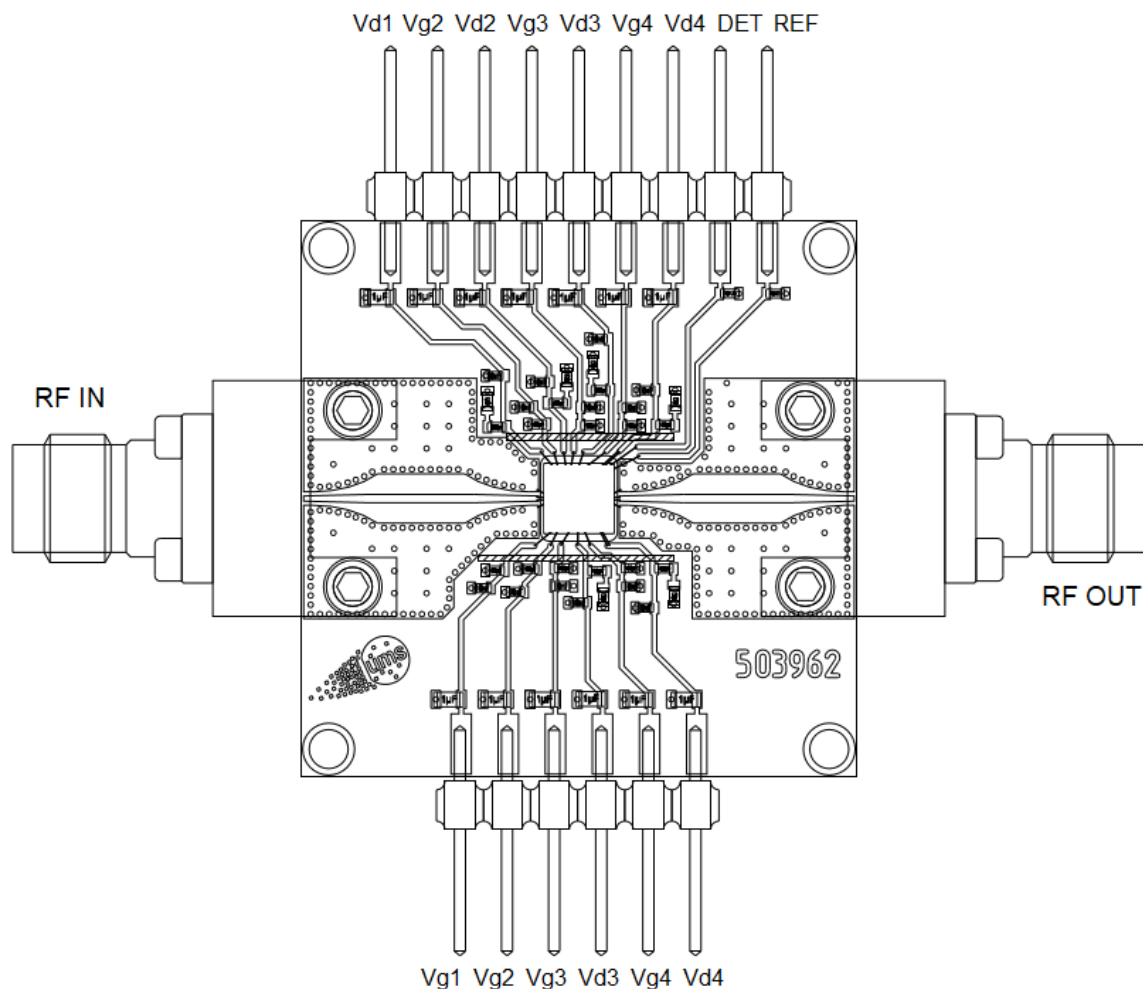


Decoupling capacitors: 100pF, 10nF & 1µF (on gate & drain access)

Note: Supply feed should be bypassed. 25µm diameter gold wire is to be preferred.

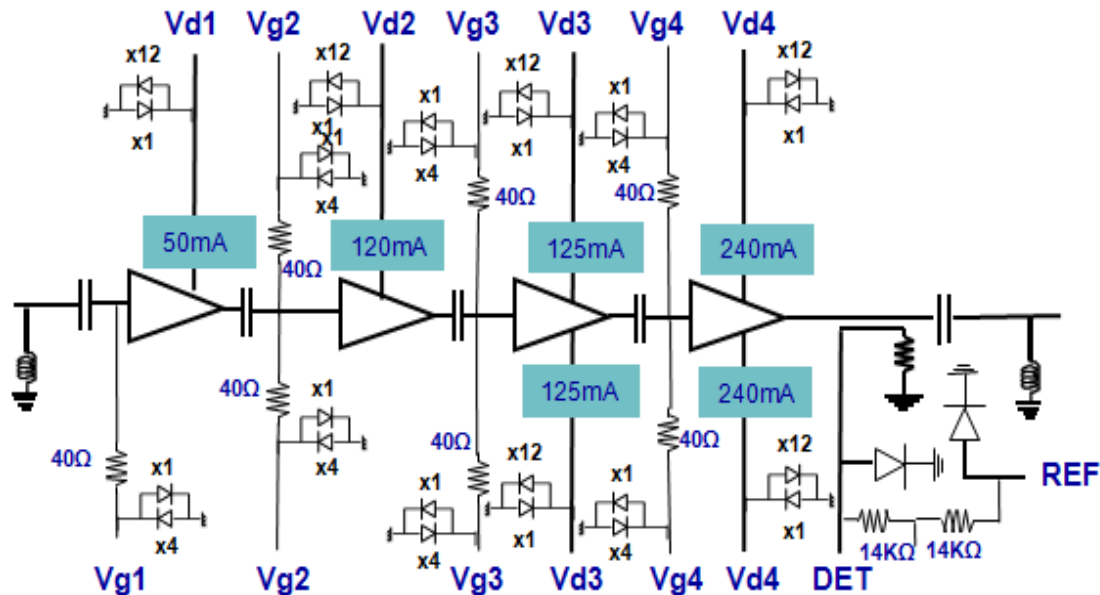
Evaluation mother board

- Compatible with the proposed footprint.
- Based on typically RF35P / 8mils or equivalent.
- Using a micro-strip to coplanar transition to access the chip.
- Recommended for the implementation of this product on a module board.
- Decoupling capacitors of 100pF $\pm 5\%$, 10nF $\pm 10\%$ and 1 μ F $\pm 10\%$ are recommended for the gate and drain accesses.
- A 10K Ω resistor is recommended on V_REF & V_DET accesses for the detector
- Note: All board measurements are performed using shielded cables, even for DC bias, to ensure safe operation.



DC Schematic

HPA : 6V, 900mA



Biasing procedure

Device Power Up instructions:

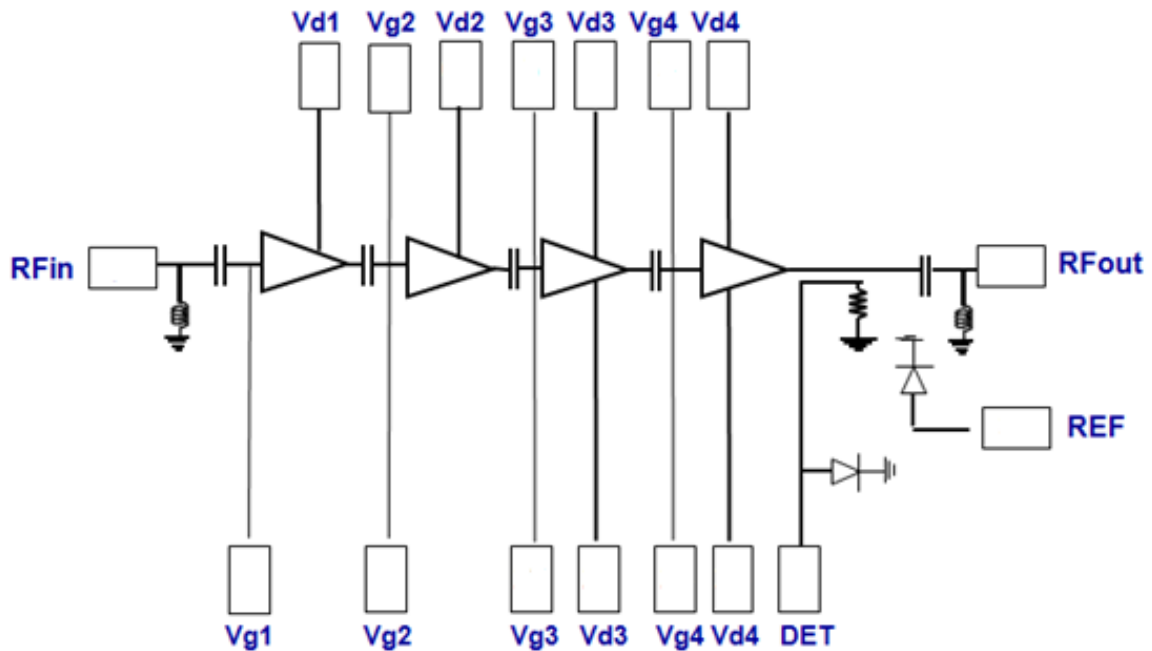
1. Ground the device
2. Bias HPA gate voltage at Vgs close to Vpinch-off (example: $V_g \approx -2V$)
3. Apply Vds quiescent bias voltage (Example: $V_d = 6V$)
4. Increase slowly Vgs up to quiescent bias drain current Idq (pulsed applied on the gate)
5. Apply RF input power

Device Power Up instructions:

1. Remove RF input power
2. Decrease HPA gate voltage up to Vgs -2V
3. Decrease drain voltage up to 0V

Notes

Due to ESD protection circuits on RF input and output, an external capacitance might be requested to isolate the product from external voltage potentially present on the RF accesses.



Limited DC decoupling is implemented on chip. Additional external DC decoupling (100pF, 10nF, 1μF) on the PC Board, as close as possible to the bare die, is required.

A 10KΩ resistor is recommended in parallel to V_DET, and V_REF accesses.

The circuit includes ESD protections on all RF and DC accesses.

Recommended ESD management

Refer to the application note AN0020 available at <https://www.ums-rf.com> for ESD sensitivity and handling recommendations for the UMS products.

Recommended environmental management

UMS products are compliant with the regulation in particular with the directives RoHS N°2011/65 and REACH N°1907/2006. More environmental data are available in the application note AN0019 also available at <https://www.ums-rf.com>.

Ordering Information

Chip form:

CHA6653-98F/00

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